

N-Channel Enhancement Mode Power MOSFET

- Features**

$V_{DS} = 65V$,

$I_D = 54A$

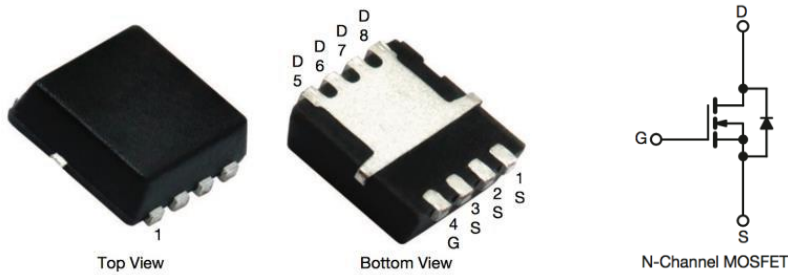
$R_{DS(ON)} @ V_{GS} = 10V$, TYP 7mΩ

$R_{DS(ON)} @ V_{GS} = 4.5V$, TYP 10.5mΩ

- General Description**

- load switch
- power supply
- synchronous rectifier

- Pin Configurations**



PDFN3*3-8L

- Absolute Maximum Ratings @ $T_A=25^\circ C$ unless otherwise noted**

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	65	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current (Continuous) *AC	$T_C=25^\circ C$	I_D	54	A
	$T_C=70^\circ C$		43	
Drain Current (Pulse) *B		I_{DM}	216	A
Power Dissipation		P_D	42	W
Operating Temperature/ Storage Temperature		T_J/T_{STG}	-55~150	$^\circ C$

- Thermal Resistance Ratings**

Parameter		Symbol	Maximum	Unit
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3	$^\circ C/W$

● Electrical Characteristics @T_A=25°C unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static *D						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	65	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	--	--	1	μA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _{DS} = 250μA	1	--	3	V
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	--	--	±100	nA
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A	--	7	9	mΩ
	R _{DS(on)}	V _{GS} = 4.5V, I _D = 10A	--	10.5	14	mΩ
Diode Forward Voltage	V _{SD}	I _{SD} = 1A, V _{GS} = 0V	--	--	1.2	V
Diode Forward Current *AB	I _S	T _C = 25°C	--	--	35	A
Switching						
Total Gate Charge	Q _g	V _{GS} =30V, V _{DS} =10V, I _{DS} =12 A	--	27	--	nC
Gate-Source Charge	Q _{gs}		--	6.4	--	nC
Gate-Drain Charge	Q _{gd}		--	6.3	--	nC
Turn-on Delay Time	t _{d(on)}	V _{DS} =30V, V _{GEN} =10V, R _G =4.5Ω, R _L =2.5Ω, I _{DS} =12 A	--	8.6	--	ns
Turn-on Rise Time	t _r		--	23.5	--	ns
Turn-off Delay Time	t _{d(off)}		--	21	--	ns
Turn-Off Fall Time	t _f		--	16	--	ns
Dynamic						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1.0MHz	--	1364	--	pF
Output Capacitance	C _{oss}		--	602	--	pF
Reverse Transfer Capacitance	C _{rss}		--	35	--	pF

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t_s ≤ 10s junction to ambient thermal resistance rating.

D: Pulse Test: Pulse Wide ≤ 300μs, Duty Cycle ≤ 2%.

● Typical Performance Characteristics (T_J = 25 °C, unless otherwise noted)

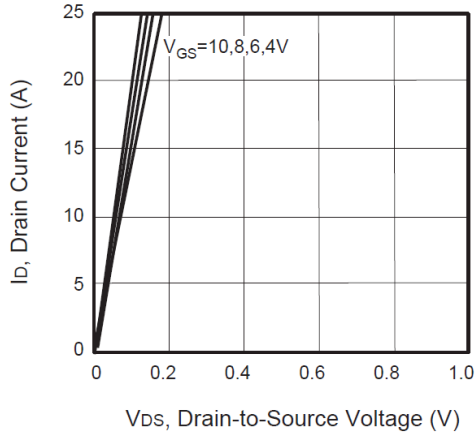


Figure 1. Output Characteristics

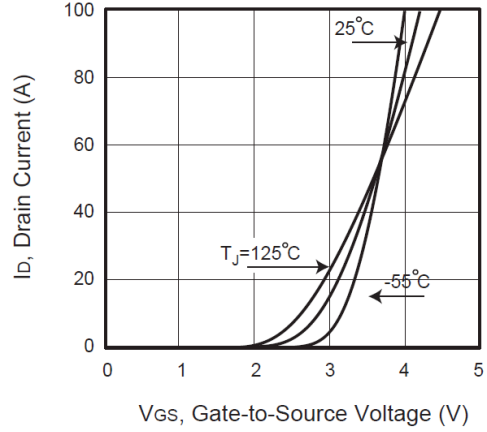


Figure 2. Transfer Characteristics

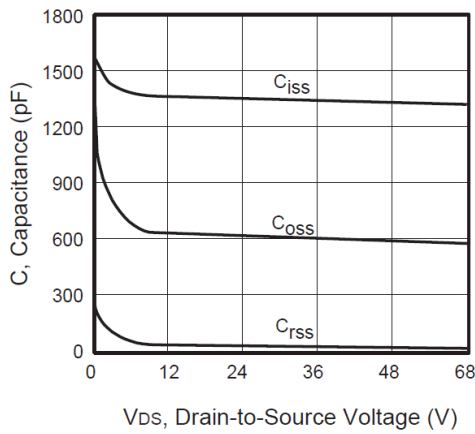


Figure 3. Capacitance

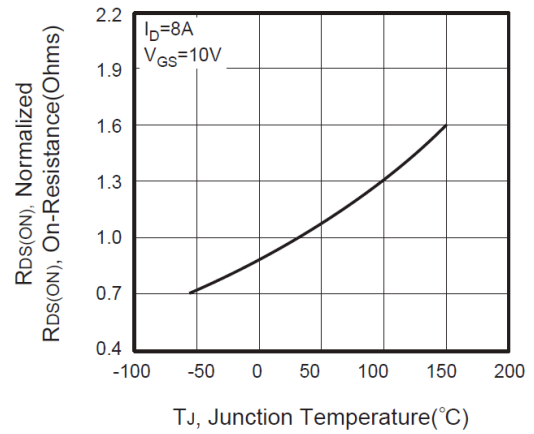


Figure 4. On-Resistance Variation with Temperature

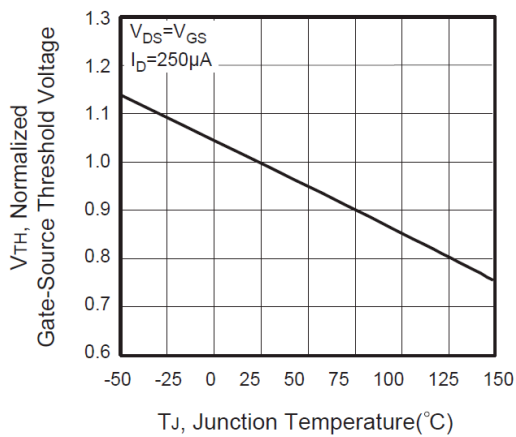


Figure 5. Gate Threshold Variation with Temperature

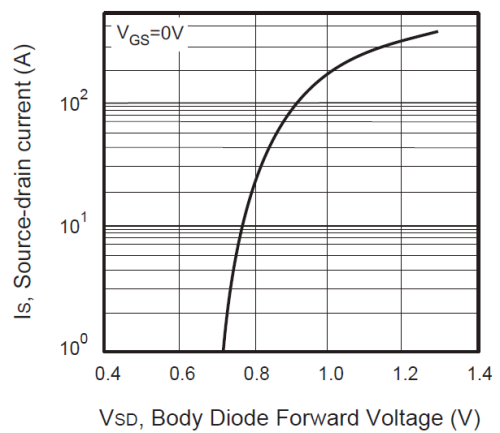


Figure 6. Body Diode Forward Voltage Variation with Source Current

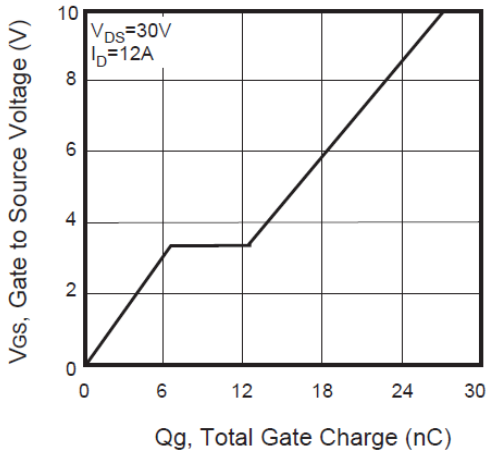


Figure 7. Gate Charge

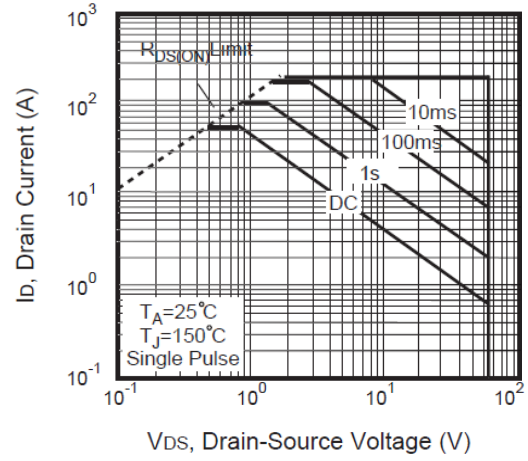


Figure 8. Maximum Safe Operating Area

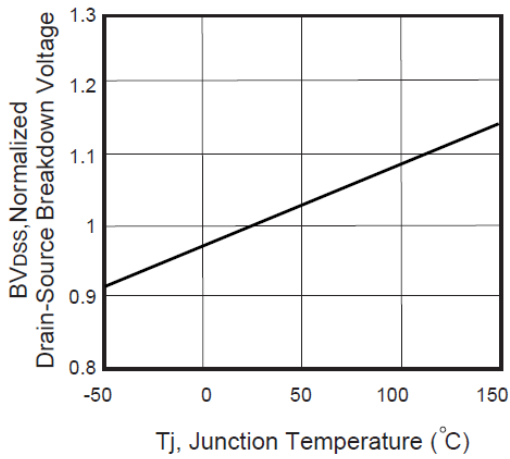


Figure 9. Breakdown Voltage Variation VS Temperature

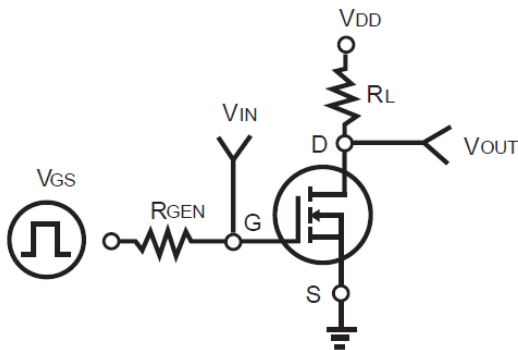


Figure 10. Switching Test Circuit

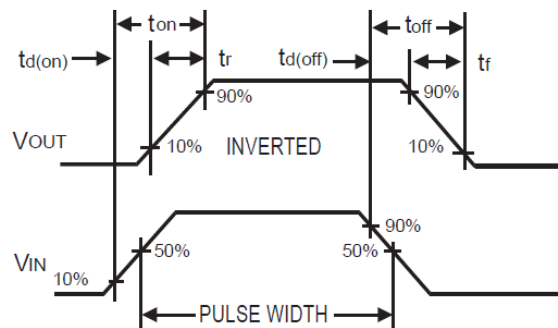


Figure 11. Switching Waveforms

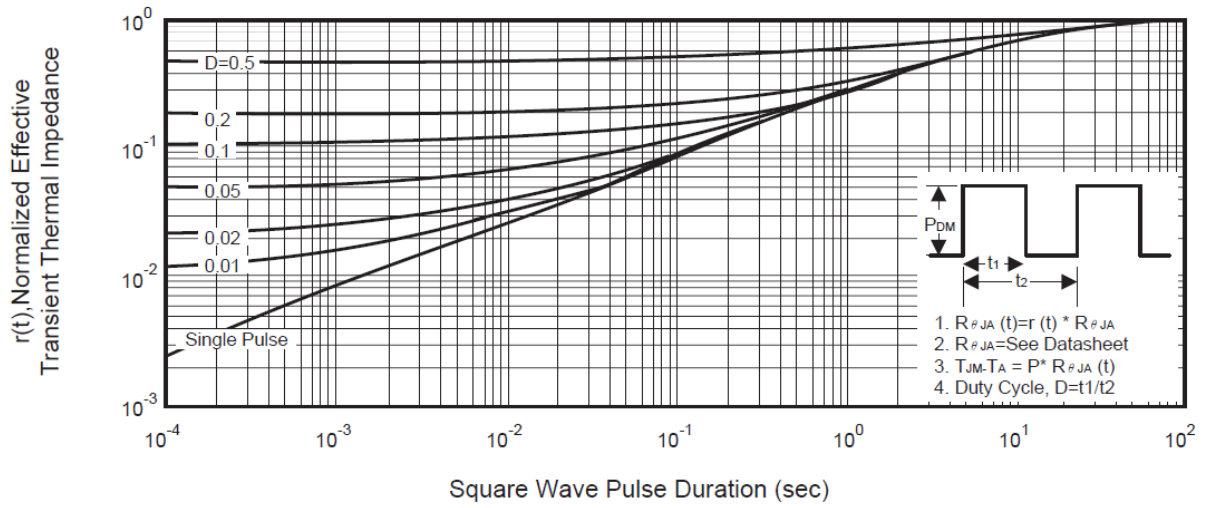
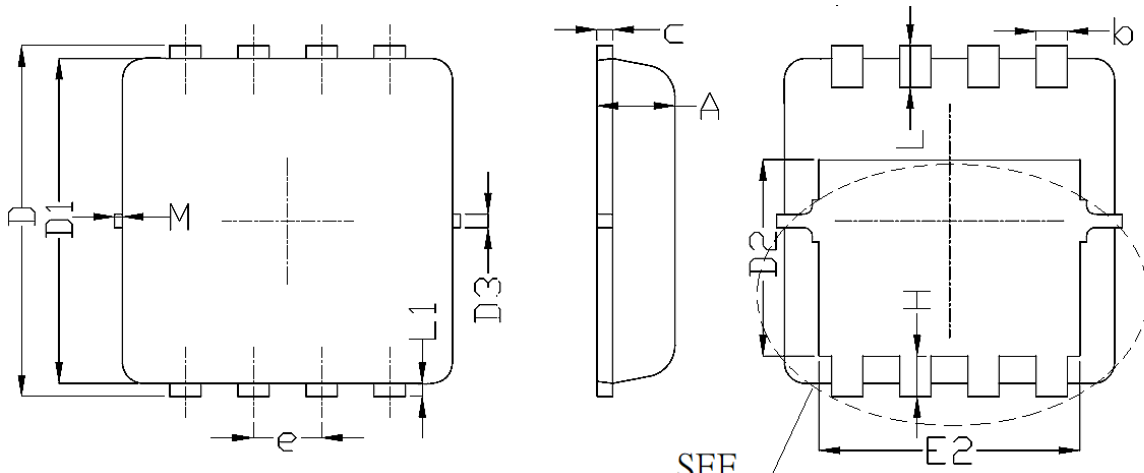
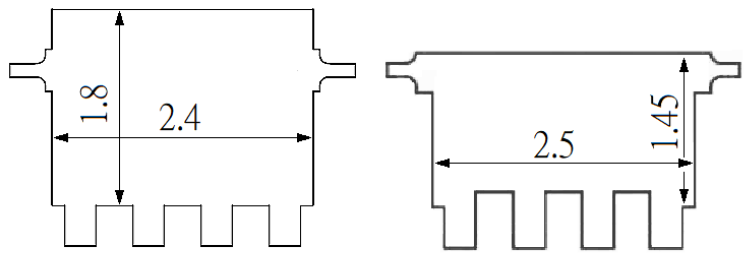
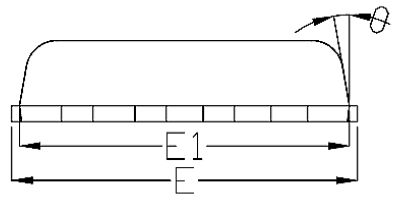


Figure 12. Normalized Thermal Transient Impedance Curve

● Package Information



SEE
DETAIL



OPTION 1

OPTION 2

DETAIL

SYMBOL	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	0.7	0.775	0.85
b	0.25	0.3	0.35
c	0.1	0.15	0.25
D	3.15	3.3	3.4
D1	2.95	3.1	3.2
D2	1.7	1.8	1.93
D3		0.13	
E	3.05	3.25	3.35
E1	2.95	3.15	3.2
E2	2.3	2.4	2.55
e	0.65 BSC		
H	0.33	0.43	0.53
L	0.3	0.4	0.5
L1	0.08	0.13	0.18
θ	-	10°	12°
M	-	-	0.15

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